

Amendments to the Claims:

This listing of claims will replace all prior version, and listings, of claims in the application:

Listing of Claims:

Claims 1 to 19. (Canceled).

20. (New) A component, comprising:
a substrate configured as a support; and
a silicon layer in which a component structure is formed, the component structure including at least one fixed element mechanically connected to the substrate via at least one anchoring element made of an anchoring material and extending through the silicon layer.
21. (New) The component of claim 20, wherein the silicon layer is connected to the substrate via a sacrificial layer, the fixed element mechanically connected to the substrate via at least one anchoring element extending through the silicon layer and the sacrificial layer.
22. (New) The component of claim 20, wherein the anchoring element is located essentially at a center of a surface of the fixed element.
23. (New) The component of claim 21, wherein the anchoring element includes a barbed structure and extends in an area of the sacrificial layer to below the silicon layer.
24. (New) The component of claim 20, wherein the anchoring element is configured to anchor an electrode and the anchoring material is electrically non-conductive.
25. (New) The component of claim 24, wherein a surface of the electrode in at least one region around the anchoring element includes a coating made of the anchoring material.
26. (New) The component of claim 25, wherein the coating extends essentially over an entire surface of the electrode, and at least one contact hole is formed in the coating for the electrode, the contact hole located outside the region around the anchoring element.

27. (New) The component of claim 24, wherein a cap diaphragm is formed on top of the component, the at least one electrode is electrically contacted via the cap diaphragm and the cap diaphragm is mechanically connected to the substrate via the anchoring element.

28. (New) The component of claim 20, wherein the anchoring material includes one of (a) silicon nitride and (b) silicon carbide.

29. (New) A method for manufacturing a component including at least one fixed element produced in a silicon layer, the silicon layer connected to a substrate via a first sacrificial layer, comprising:

(a) making at least one recess in the silicon layer in an area of a surface of the fixed element, the recess extending through the entire silicon layer and the first sacrificial layer down to the substrate; and

(b) filling the recess with an anchoring material to mechanically connect the fixed element to the substrate via an anchoring element that is thereby created.

30. (New) The method of claim 29, wherein the recess in the silicon layer is made in the making step in an anisotropic etching process.

31. (New) The method of claim 29, further comprising removing the first sacrificial layer in an area of the recess in an anisotropic etching process.

32. (New) The method of claim 31, wherein the anisotropic etching process includes undercutting an edge region of the recess in the silicon layer.

33. (New) The method of claim 29, further comprising:

depositing the anchoring material on the silicon layer to grow on the substrate in an area of the recess and fills the recess; and

at least partly removing an anchoring material coating of the silicon layer created by the depositing of the anchoring material.

34. (New) The method of claim 29, further comprising:

forming a cap diaphragm on the component;

producing a second sacrificial layer having a continuous surface on top of the component that is defined in the silicon layer and in which at least one electrode having at least one anchoring element is already formed;

patterning the second sacrificial layer;

removing the second sacrificial layer in an area of the anchoring element and in an area of at least one contact point on the surface of the electrode;

producing a diaphragm layer on top of the patterned second sacrificial layer; patterning the diaphragm layer;

creating openings for removing the second sacrificial layer;

creating openings through which an electrical connection of the electrode to the diaphragm layer is electrically insulated from remaining areas of the diaphragm layer; and

removing at least the second sacrificial layer.

35. (New) The method of claim 34, wherein the diaphragm layer is produced in the diaphragm layer producing step from one of (a) polysilicon and (b) SiGe.

36. (New) The method of claim 34, wherein the diaphragm layer is grown epitactically from polysilicon.

37. (New) The method of claim 36, wherein the diaphragm layer is patterned using trench etching.

38. (New) The method of claim 34, wherein the second sacrificial layer is produced in the second sacrificial layer producing step from silicon oxide.

39. (New) The component of claim 20, wherein the component is configured as a sensor element.

40. (New) The component of claim 20, wherein the at least one fixed element includes an electrode.

41. (New) The method of claim 29, wherein the component is configured as a sensor element.

42. (New) The method of claim 29, wherein the at least one fixed element includes an electrode.

43. (New) The method of claim 30, wherein the recess in the silicon layer is produced by trenching.

44. (New) The method of claim 31, wherein the first sacrificial layer in the area of the recess is removed by trenching.

45. (New) The method of claim 34, wherein openings are created for removing the second and also the first sacrificial layer.

46. (New) The method of claim 34, wherein the second sacrificial layer is removed using HF vapor etching.